

## Low voltage fast-switching PNP power transistors

### Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed

### Applications

- LED
- Motherboard & hard disk drive
- Mobile equipment
- DC-DC converter

### Description

The devices are PNP transistors manufactured using new "PB-HDC" (power bipolar high density current) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

The 2STF2340 complementary PNP is the 2STF1340.

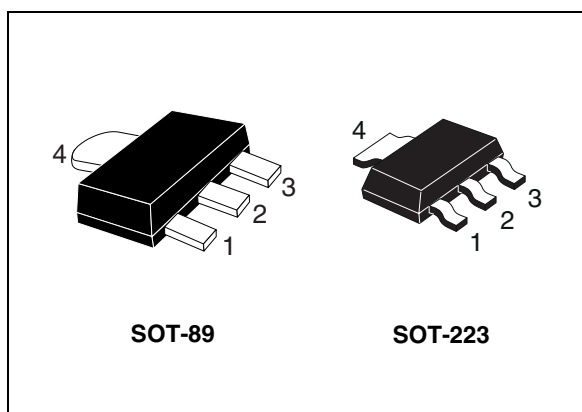


Figure 1. Internal schematic diagram

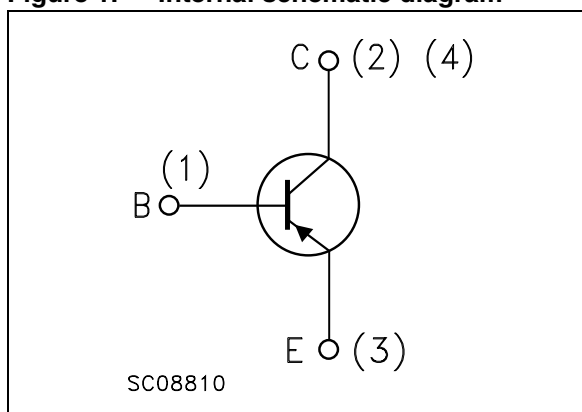


Table 1. Device summary

Order codes	Marking	Packages	Packaging
2STF2340	2340	SOT-89	Tape and reel
2STN2340	N2340	SOT-223	Tape and reel

# 1 Electrical ratings

**Table 2. Absolute maximum rating**

Symbol	Parameter	Value		Unit
		2STF2340	2STN2340	
		SOT-89	SOT-223	
$V_{CES}$	Collector-emitter voltage ( $V_{BE} = 0$ )	-40		V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	-40		V
$V_{EBO}$	Emitter-base voltage ( $I_C = 0$ )	-5		V
$I_C$	Collector current	-3		A
$I_{CM}$	Collector peak current ( $t_p < 5$ ms)	-6		A
$P_{TOT}$	Total dissipation at $T_{amb} = 25$ °C	1.4	1.6	W
$T_{STG}$	Storage temperature	-65 to 150		°C
$T_J$	Max. operating junction temperature	150		°C

**Table 3. Thermal data**

Symbol	Parameter	SOT-89	SOT-223	Unit
$R_{thJA}^{(1)}$	Thermal resistance junction-ambient max	89	78	°C/W

1. Device mounted on PCB area of 1 cm<sup>2</sup>

## 2 Electrical characteristics

$T_{\text{case}} = 25\text{ }^{\circ}\text{C}$  unless otherwise specified

**Table 4. Electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{\text{CBO}}$	Collector cut-off current ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = -40\text{ V}$			-0.1	$\mu\text{A}$
$I_{\text{EBO}}$	Emitter cut-off current ( $I_{\text{C}} = 0$ )	$V_{\text{EB}} = -5\text{ V}$			-0.1	$\mu\text{A}$
$V_{(\text{BR})\text{CBO}}^{(1)}$	Collector-base breakdown voltage ( $I_{\text{E}} = 0$ )	$I_{\text{C}} = -100\text{ }\mu\text{A}$	-40			V
$V_{(\text{BR})\text{CEO}}^{(1)}$	Collector-emitter breakdown voltage ( $I_{\text{B}} = 0$ )	$I_{\text{C}} = -10\text{ mA}$	-40			V
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ( $I_{\text{C}} = 0$ )	$I_{\text{E}} = -100\text{ }\mu\text{A}$	-5			V
$V_{\text{CE}(\text{sat})}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = -2\text{ A}$ $I_{\text{B}} = -100\text{ mA}$ $I_{\text{C}} = -3\text{ A}$ $I_{\text{B}} = -150\text{ mA}$			-250 -350	mV mV
$V_{\text{BE}(\text{sat})}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = -2\text{ A}$ $I_{\text{B}} = -100\text{ mA}$			-1.2	V
$h_{\text{FE}}^{(1)}$	DC current gain	$I_{\text{C}} = -0.1\text{ A}$ $V_{\text{CE}} = -2\text{ V}$ $I_{\text{C}} = -1\text{ A}$ $V_{\text{CE}} = -2\text{ V}$ $I_{\text{C}} = -3\text{ A}$ $V_{\text{CE}} = -2\text{ V}$	100 180	220	450	
$f_{\text{t}}$	Transition frequency	$I_{\text{C}} = -0.1\text{ A}$ $V_{\text{CE}} = -5\text{ V}$ $f = 100\text{ MHz}$	100			MHz
$C_{\text{CBO}}$	Collector-base capacitance ( $I_{\text{E}} = 0$ )	$V_{\text{CB}} = -10\text{ V}$ $f = 1\text{ MHz}$		50		pF
$t_{\text{on}}$ $t_{\text{off}}$	Resistive load Turn-on time Turn-off time	$I_{\text{C}} = -1.5\text{ A}$ $V_{\text{CC}} = -10\text{ V}$ $I_{\text{B}(\text{on})} = -I_{\text{B}(\text{off})} = -150\text{ mA}$ $V_{\text{BB}(\text{off})} = 5\text{ V}$		80 450		ns ns

1. Pulse test: pulse duration  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

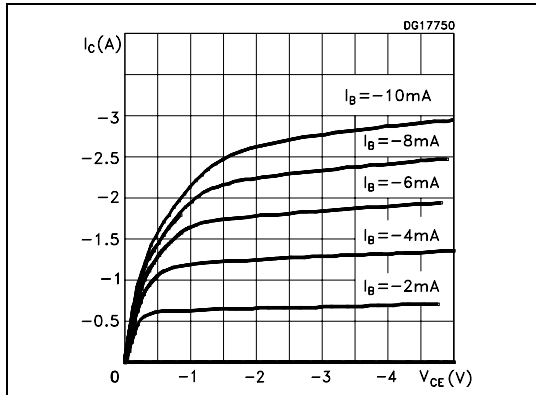


Figure 3. Derating curve

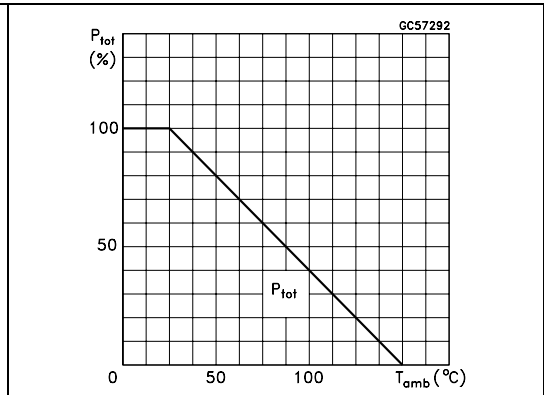


Figure 4. DC current gain ( $V_{CE} = -2$  V)

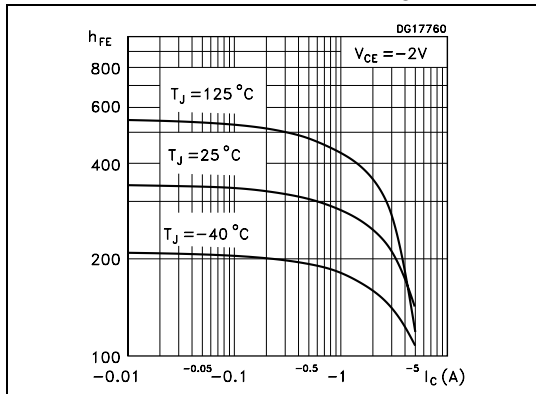


Figure 5. DC current gain ( $V_{CE} = -5$  V)

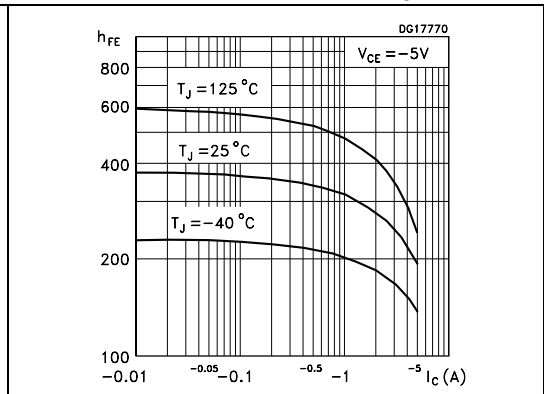


Figure 6. Collector-emitter saturation voltage

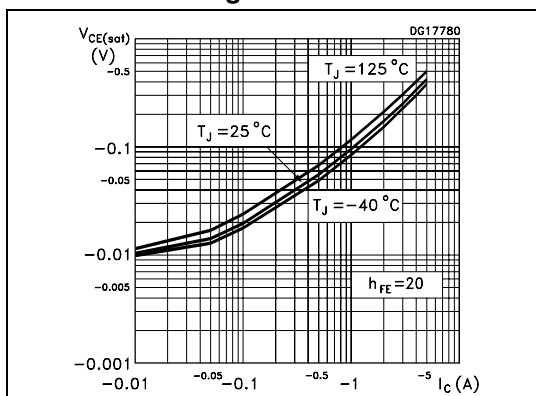


Figure 7. Base-emitter saturation voltage

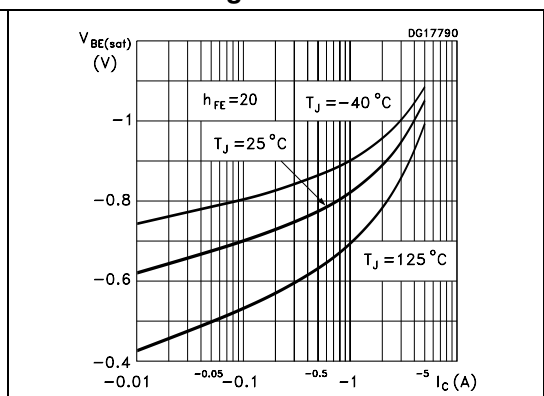


Figure 8. Resistive load switching on

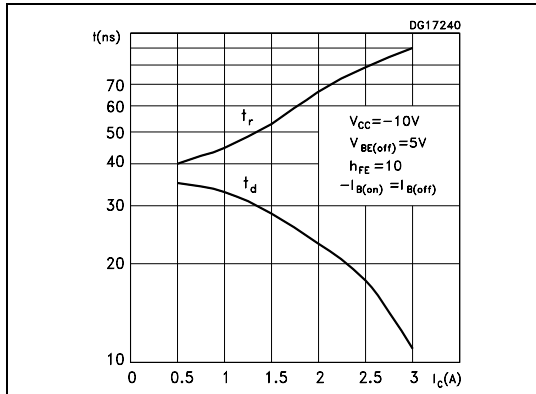


Figure 9. Resistive load switching off

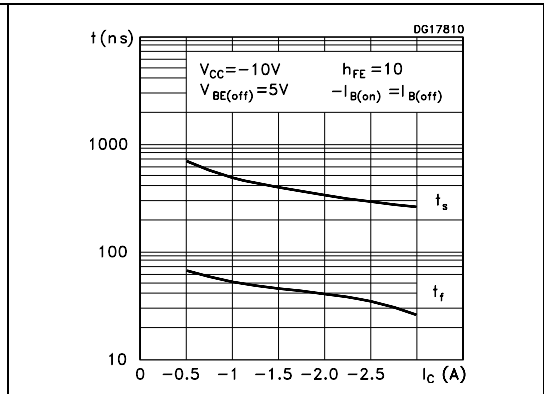
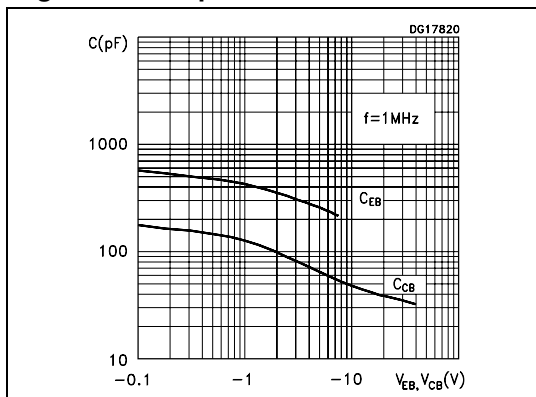
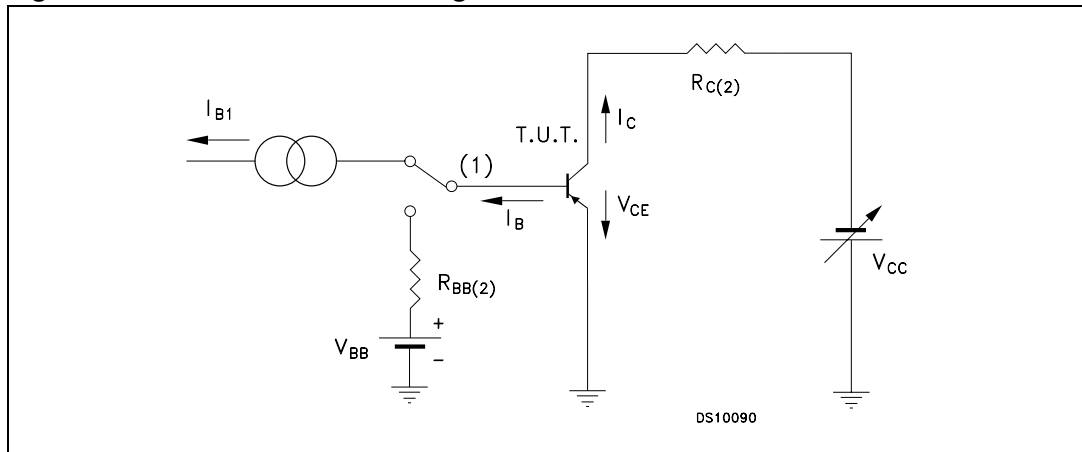


Figure 10. Capacitance curves



## 2.2 Test circuits

Figure 11. Resistive load switching test circuit



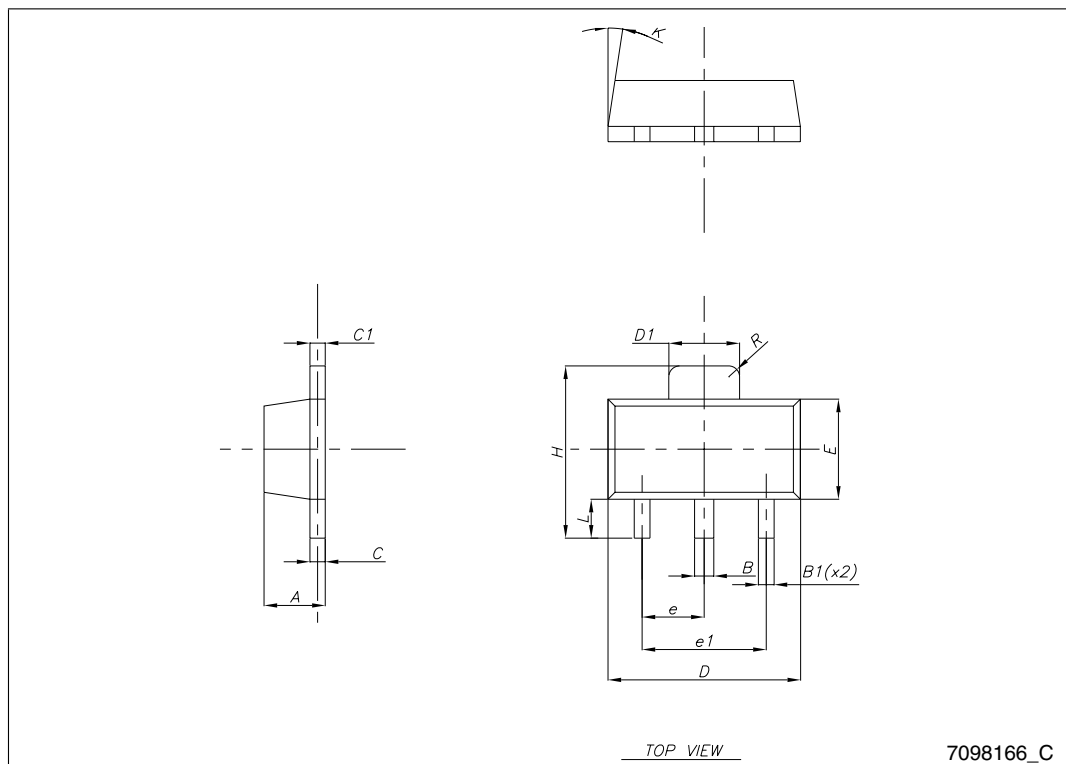
1. Fast electronic switch
2. Non-inductive resistor

### 3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

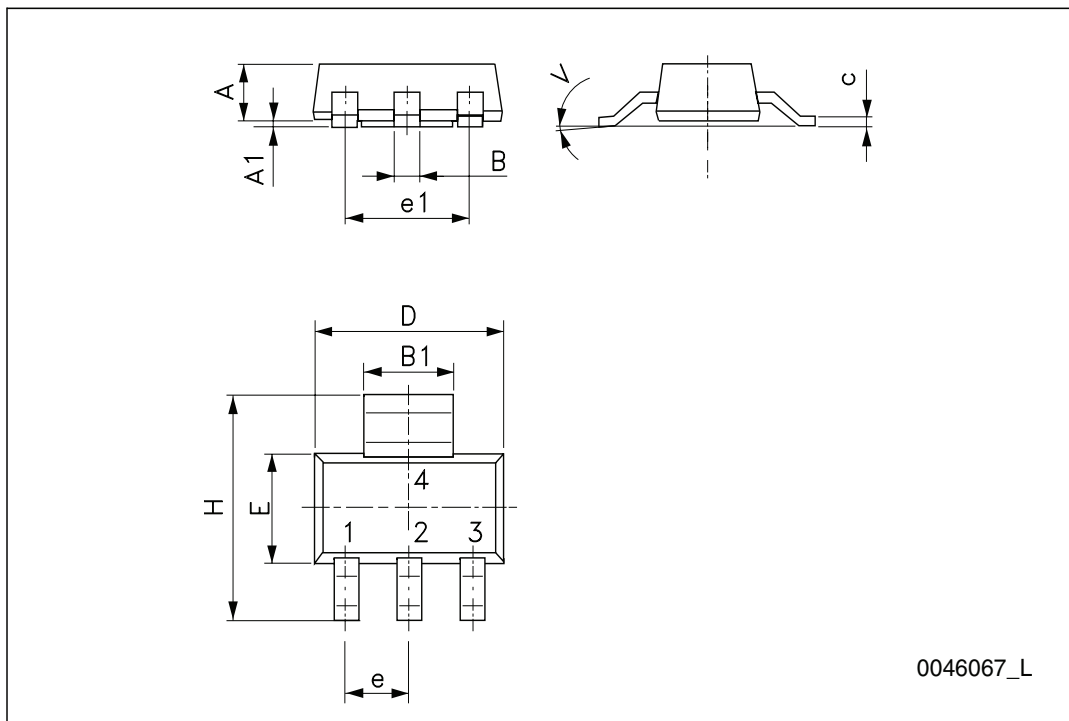
## SOT-89 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	1.40		1.60
B	0.44		0.56
B1	0.36		0.48
C	0.35		0.44
C1	0.35		0.44
D	4.40		4.60
D1	1.62		1.83
E	2.29		2.60
e	1.42		1.57
e1	2.92		3.07
H	3.94		4.25
K	1°		8°
L	0.89		1.20
R		0.25	



**SOT-223 mechanical data**

DIM.	mm.		
	min.	typ	max.
A			1.80
A1	0.02		0.1
B	0.60	0.70	0.85
B1	2.90	3.00	3.15
c	0.24	0.26	0.35
D	6.30	6.50	6.70
e		2.30	
e1		4.60	
E	3.30	3.50	3.70
H	6.70	7.00	7.30
V			10°



0046067\_L



## 4 Revision history

**Table 5. Document revision history**

<b>Date</b>	<b>Revision</b>	<b>Changes</b>
04-Dec-2007	1	Initial release.
19-Oct-2009	2	Inserted 2STN2340 in SOT-223 package.

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